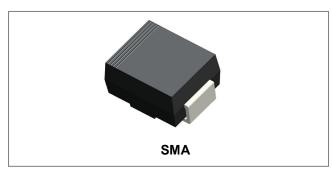






10MQ150N SCHOTTKY RECTIFIER



Features

- Small foot print, surface moutable
- Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Applications

- Disk Drives
- Switching power supply
- Redundant power subsystems
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Battery Charging

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$egin{array}{c} V_{RRM} \ V_{RWM} \ V_{R} \end{array}$	-	150	V
Average Forward Current	I _{F(AV)}	50% duty cycle @T _L =123°C, rectangular wave form On PC board 9mm² island	1	А
Peak One Cycle Non-Repetitive Surge Current	I _{FSM}	8.3 ms, half Sine pulse, T _C = 25 °C	20	Α

Electrical Characteristics:

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*	V _{F1}	@ 1 A, Pulse, T _J = 25 °C	0.79	0.86	V
	V _{F2}	@ 1 A, Pulse, T _J = 100 °C	-	0.70	V
Reverse Current*	I_{R1}	$@V_R = Rated V_R, Pulse, T_J = 25 °C$	0.0001	0.5	mA
	I_{R2}	$@V_R = Rated V_R, Pulse, T_J = 125 °C$	0.05	1	mA
Junction Capacitance	Ст	$@V_R = 5V, T_C = 25 °C$ $f_{SIG} = 1MHz$	25	45	PF
Typical Series Inductance	Ls	Measured lead to lead 5 mm from package body	2.0	-	nH
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

^{*} Pulse width < 300 µs, duty cycle < 2%





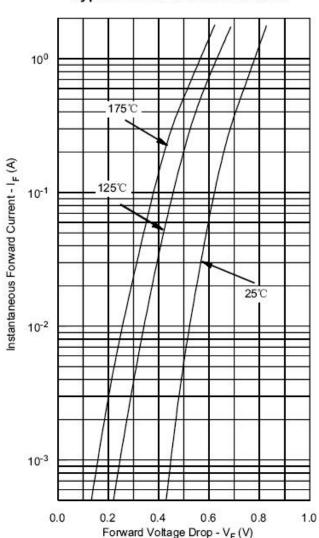


Thermal-Mechanical Specifications:

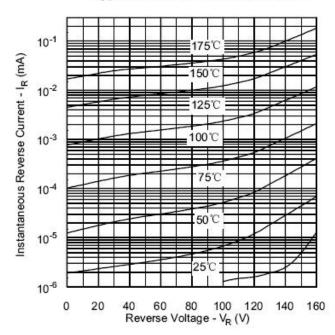
Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +175	°C
Storage Temperature	T _{stg}	-	-55 to +175	°C
Typical Thermal Resistance Junction to Ambient	$R_{\theta JA}$	-	80	°C/W
Approximate Weight	wt	-	0.06	g
Case Style	SMA			

Ratings and Characteristics Curves

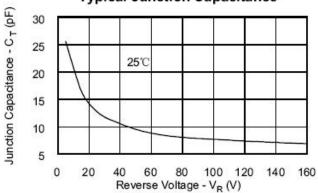
Typical Forward Characteristics



Typical Reverse Characteristics



Typical Junction Capacitance



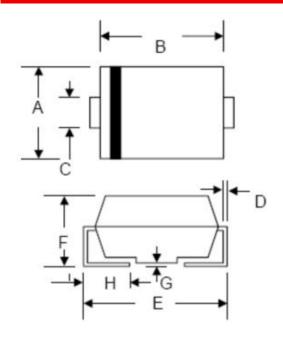
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Mechanical Dimensions SMA



CVMDOL	Millimeters		Inches	
SYMBOL	Min.	Max.	Min.	Max.
Α	2.40	2.84	0.094	0.112
В	3.99	4.75	0.157	0.187
С	1.05	1.70	0.041	0.067
D	0.15	0.51	0.006	0.020
E	4.80	5.66	0.189	0.223
F	1.90	2.95	0.075	0.116
G	0.05	0.203	0.002	0.008
Н	0.76	1.52	0.030	0.600

Ordering Information

Device	Package	Shipping	
10MQ150N	SMA (Pb-Free)	5000pcs / reel	

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Marking Diagram

Where XXXXX is YYWWL



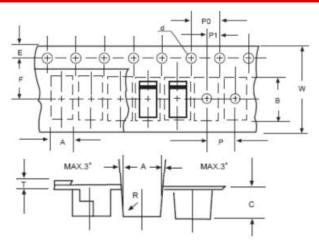
S = Device Type
A = Package Type
1 = Forward Current (1A)
M = Reverse Voltage (150V)
YY = Year
WW = Week

= Lot Number

Cautions: Molding resin

Epoxv resin UL:94V-0

Carrier Tape & Reel Specification SMA



SYMBOL	Millimeters		
STWIBUL	Min.	Max.	
Α	2.97	3.17	
В	5.70	5.90	
C	2.32	2.52	
d	1.40	1.60	
E	1.40	1.60	
F	5.60	5.70	
Р	3.90	4.10	
P0	3.90	4.10	
P1	1.90	2.10	
Т	0.25	0.35	
W	11.80	12.20	

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